

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

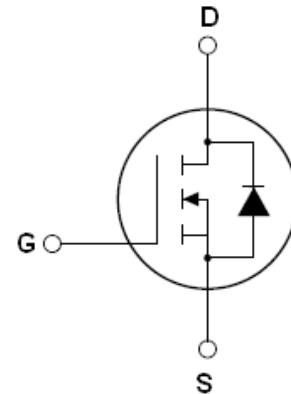
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

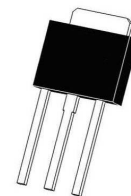
V_{DS}	800	V
$R_{DS(ON)TYP}$	1290	m Ω
I_D	5	A



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
HMS5N80I	TO-251	HMS5N80I
HMS5N80K	TO-252	HMS5N80K



TO-251



TO-252

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	800	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	5	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	3	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	20	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	46	W
Derate above 25°C		0.37	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note2)	E_{AS}	52	mJ
Avalanche current (Note 1)	I_{AR}	0.9	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.14	mJ
Parameter	Symbol	Value	Unit

Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	2.72	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	75	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	800			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =800V, V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =800V, V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.6		4.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.5A		1290	1300	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz		370		pF
Output Capacitance	C _{Oss}			25		pF
Reverse Transfer Capacitance	C _{rss}			0.5		pF
Total Gate Charge	Q _g	V _{DS} =480V, I _D =5A, V _{GS} =10V		10.5	15	nC
Gate-Source Charge	Q _{gs}			2.6		nC
Gate-Drain Charge	Q _{gd}			5.3		nC
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =420V, I _D =3A, R _G =5Ω, V _{GS} =10V		8		nS
Turn-on Rise Time	t _r			4		nS
Turn-Off Delay Time	t _{d(off)}			55		nS
Turn-Off Fall Time	t _f			11		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			5	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				20	A
Forward on voltage	V _{SD}	T _j =25℃, I _{SD} =5A, V _{GS} =0V		0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _j =25℃, I _F =2.5A, di/dt=100A/μs		210		nS
Reverse Recovery Charge	Q _{rr}			0.66		uC
Peak reverse recovery current	I _{rrm}			6.5		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

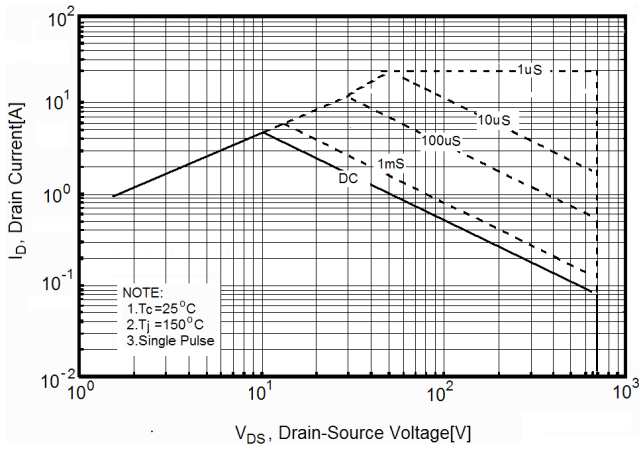


Figure2. Source-Drain Diode Forward Voltage

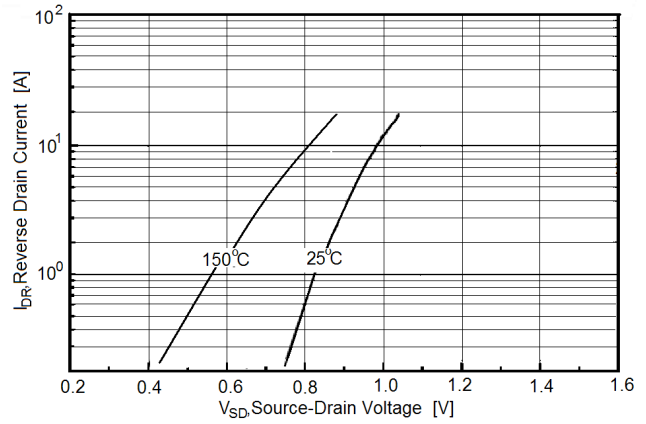


Figure3. Output characteristics

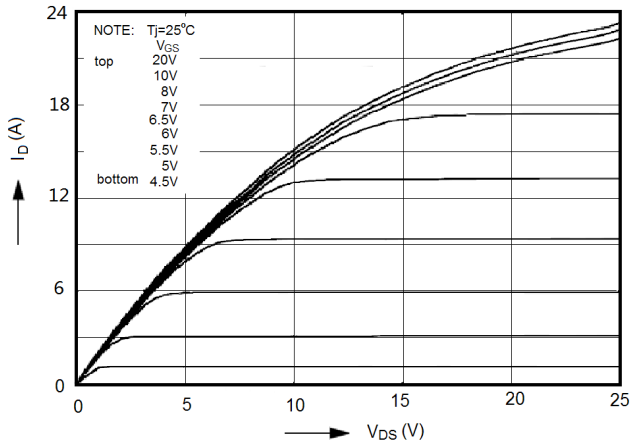


Figure4. Transfer characteristics

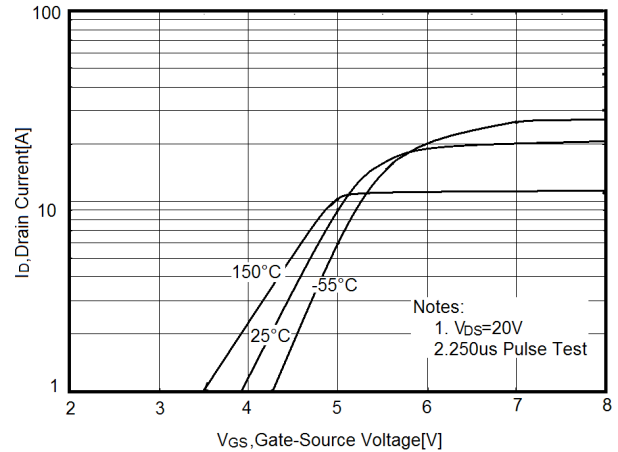


Figure5. Static drain-source on resistance

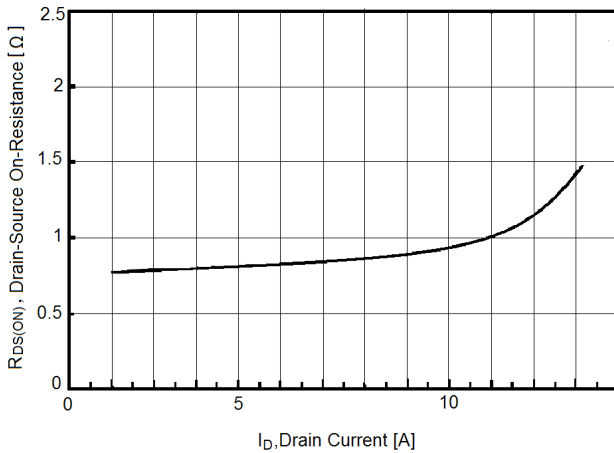


Figure6. $R_{DS(ON)}$ vs Junction Temperature

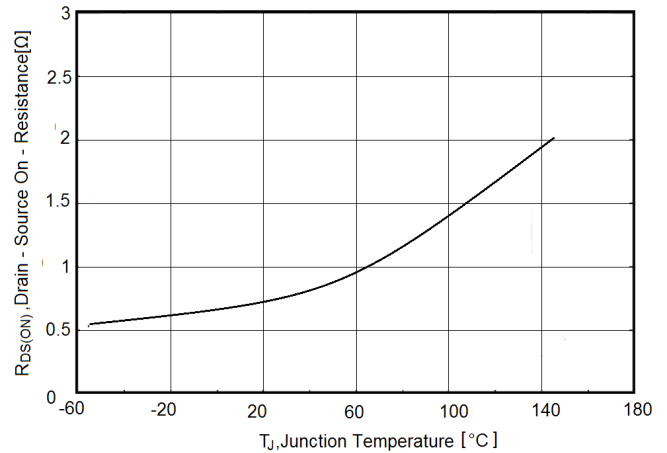


Figure7. BV_{DSS} vs Junction Temperature

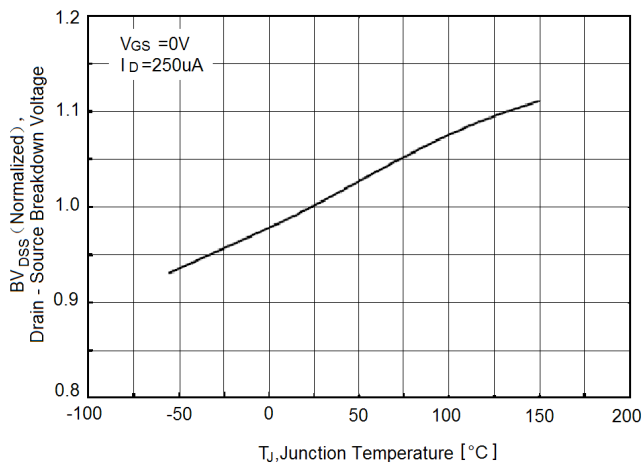


Figure9. Gate charge waveforms

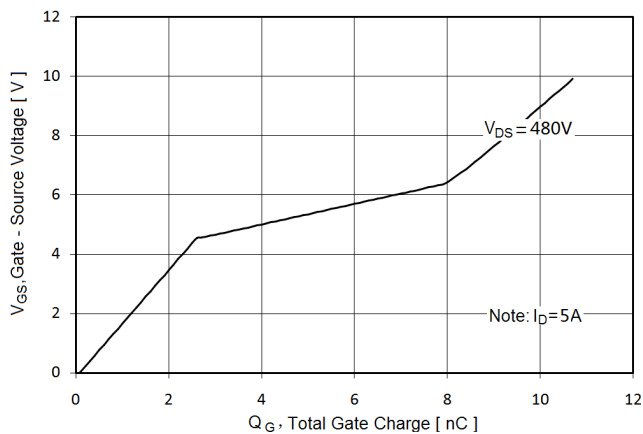


Figure11. Transient Thermal Impedance

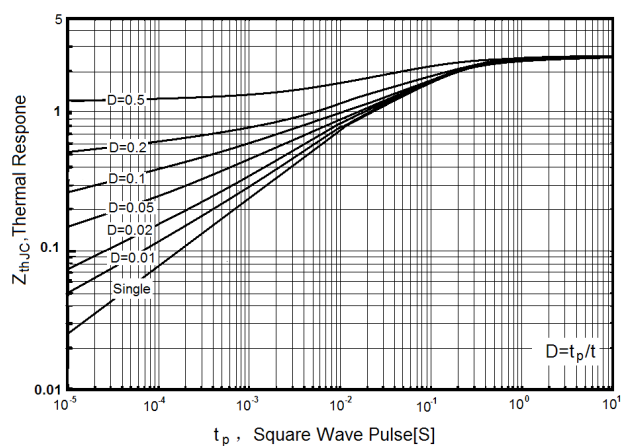


Figure8. Maximum I_D vs Junction Temperature

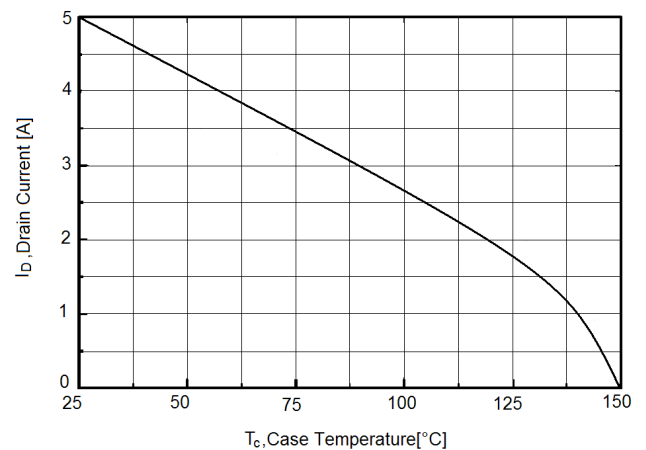
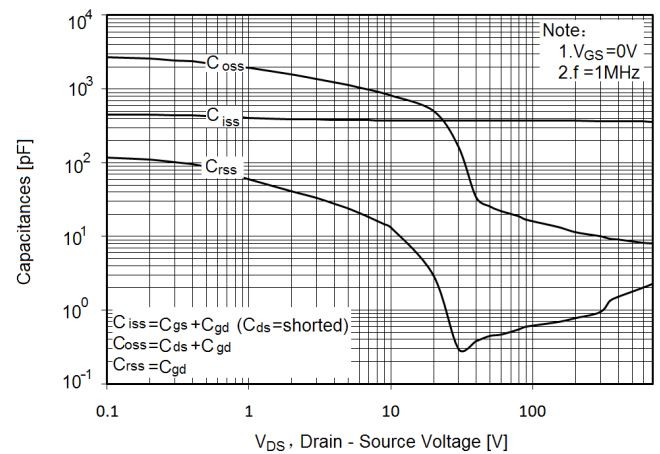
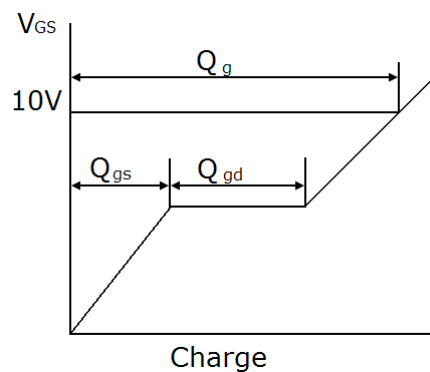
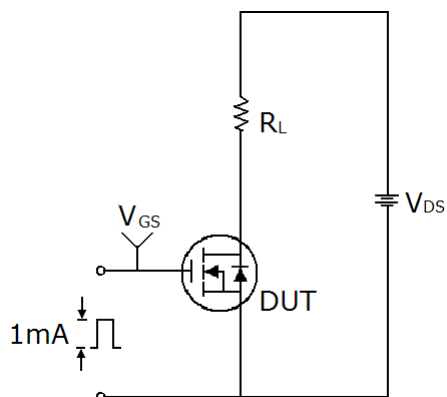


Figure10. Capacitance

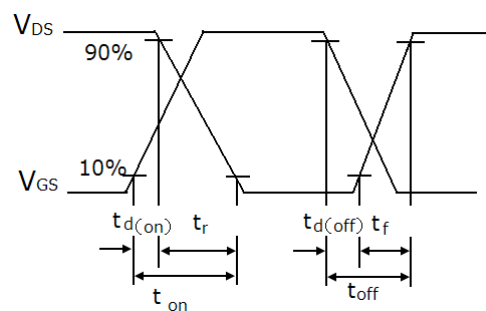
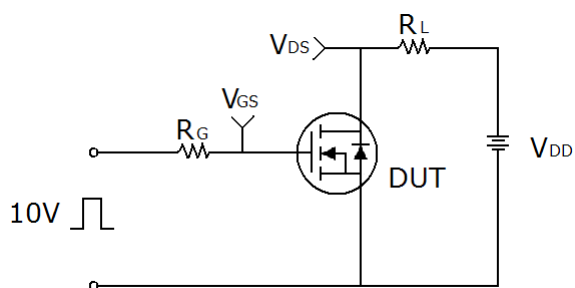


Test circuit

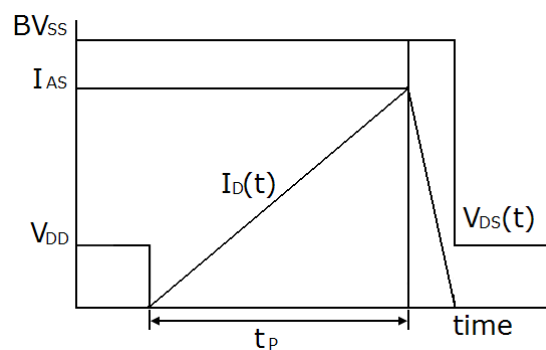
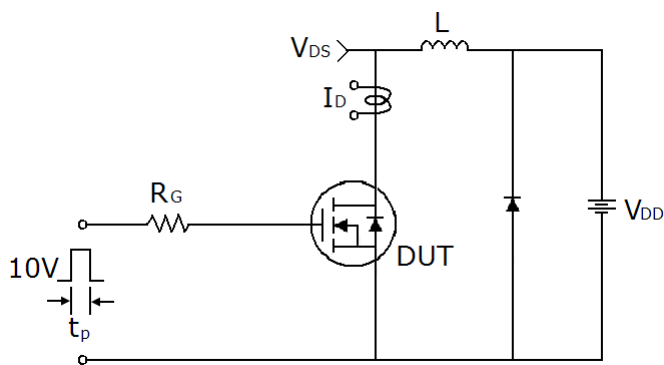
1) Gate charge test circuit & Waveform



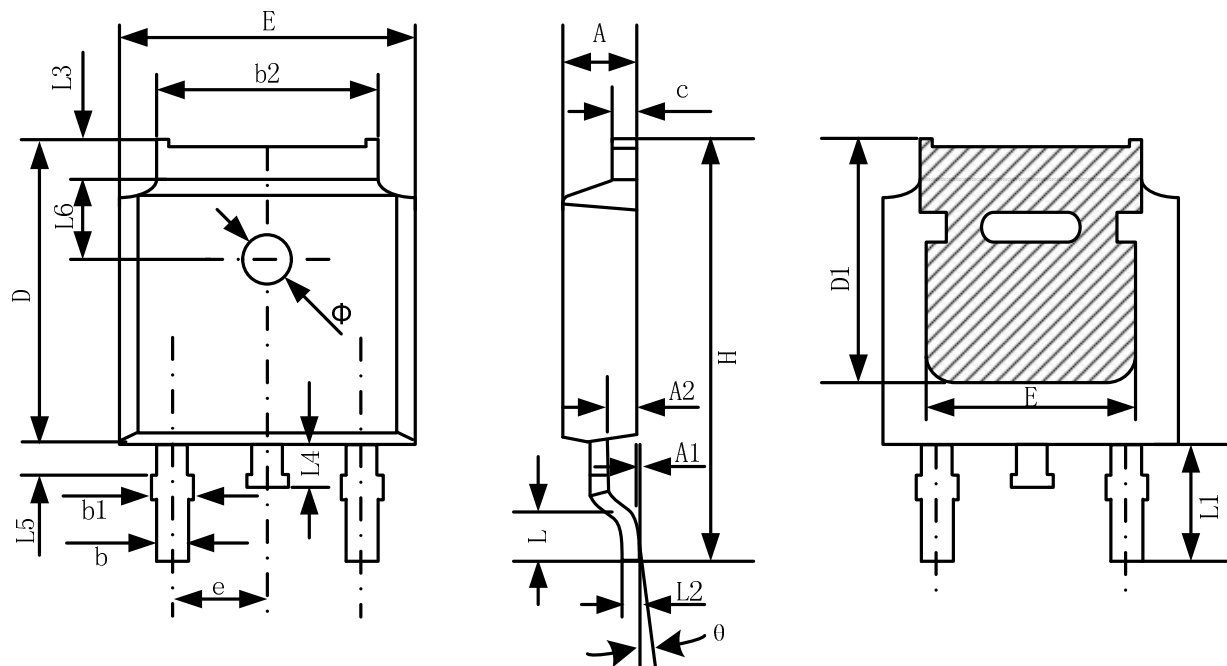
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

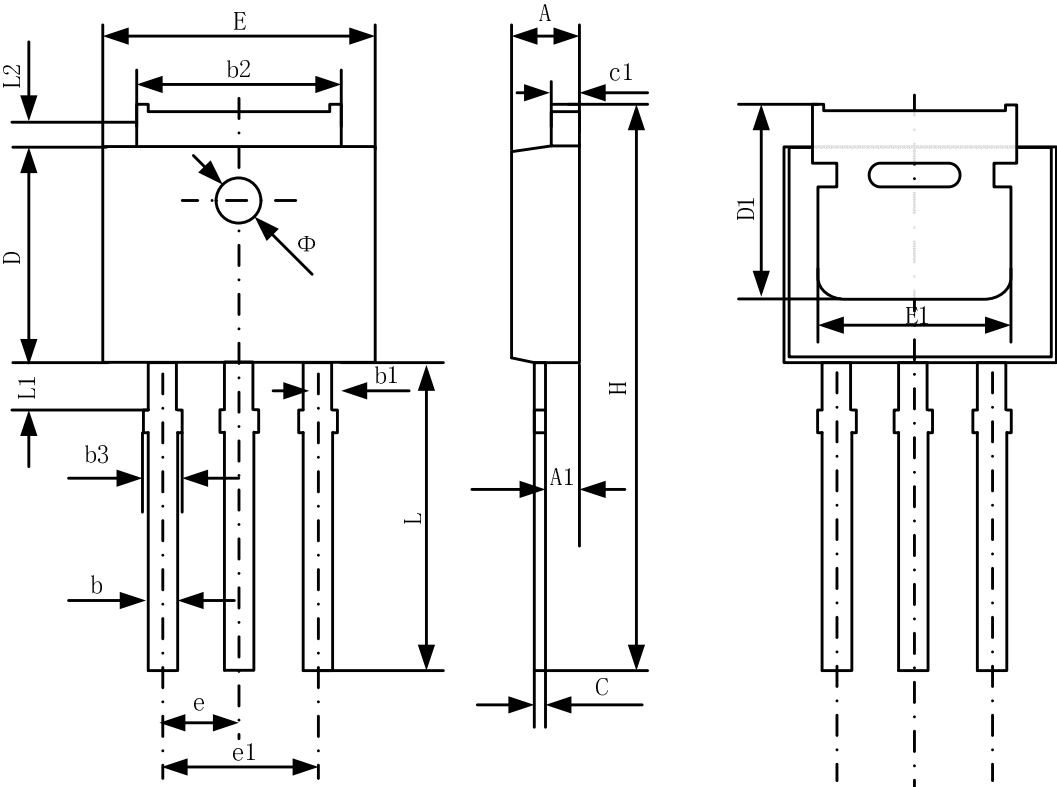


TO-252-2 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.38	0.087	0.094
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.72	0.85	0.028	0.033
b1	0.72	0.90	0.028	0.035
b2	5.13	5.46	0.202	0.215
c	0.47	0.60	0.019	0.024
D	6.00	6.20	0.236	0.244
D1	5.25	--	0.207	--
E	6.50	6.70	0.256	0.264
E1	4.70	--	0.185	--
e	2.19	2.39	0.086	0.094
H	9.80	10.40	0.386	0.409
L	1.40	1.70	0.055	0.067
L1	2.90 REF		0.114 REF	
L2	0.508 BSC		0.020 BSC	
L3	0.90	1.25	0.035	0.049
L4	0.60	1.00	0.024	0.039
L5	0.15	0.75	0.006	0.030
L6	1.80 REF		0.071 REF	
Φ	1.20	1.40	0.047	0.055
θ	0°	8°	0°	8°

TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.35	0.087	0.093
A1	0.90	1.10	0.035	0.043
b	0.56	0.69	0.022	0.027
b1	0.77	0.90	0.030	0.035
b2	5.23	5.43	0.206	0.214
b3		1.05	0.000	0.041
C	0.46	0.59	0.018	0.023
c1	0.46	0.59	0.018	0.023
D	6.00	6.20	0.236	0.244
D1	5.20		0.205	
E	6.50	6.70	0.256	0.264
E1	4.60	5.00	0.181	
e	2.24	2.34	0.088	0.092
e1	4.47	4.67	0.176	0.184
H	16.18	16.78	0.637	0.661
L	9.00	9.60	0.354	0.378
L1	0.95	1.35	0.037	0.053
L2	0.90	1.25	0.035	0.049